

Q.P Code: 23PH102

Hall Ticket No.:

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**NARSIMHAREDDY ENGINEERING COLLEGE**  
(UGC AUTONOMOUS)

I.B.Tech I Semester (NR23) Regular Examination, January/February 2024

**APPLIED PHYSICS**  
(Common to CSE, IT)

**Time : 3 hours**

**Maximum marks: 60**

- Note:**
- This question paper contains two parts, A and B
  - Part A is compulsory which carries 10 marks (10 sub questions are two from each unit carry 1 Marks). Answer all questions in Part A
  - Part B Consists of 5 Units. Answer one question from each unit. Each question carries 10 Marks and may have a, b sub questions

**Part-A**  
Answer all questions

(10 Marks)

Q.No	Question	M	CO	BL
1) a.	What are matter waves?	1	CO1	L1
b.	Mention a few drawbacks of the classical theory of the free electron.	1	CO1	L2
c.	List out the majority and minority charge in n-type and p-type semiconductors.	1	CO2	L1
d.	Draw CE, CB, and CC configurations of an n-p-n transistor.	1	CO2	L3
e.	Define electric dipole and dipole moment?	1	CO3	L1
f.	Mention a few applications of soft magnetic materials.	1	CO3	L2
g.	What is surface to volume ratio?	1	CO4	L1
h.	What are the various methods in the characterization of materials?	1	CO4	L1
i.	Differentiate between laser light and conventional light?	1	CO5	L2
j.	Why optical fiber communication is beneficial than traditional communication systems?	1	CO5	L1

**Part-B**  
Answer all the Units  
All Questions carry equal Marks

(50 Marks)

Q.No	Question	M	CO	BL
<b>UNIT-I</b>				
2) a.	Explain the photoelectric effect.	5	CO1	L2
b.	Show that $\lambda = \frac{1227}{\sqrt{V}}$ nm	5	CO1	L3
<b>OR</b>				
3) a.	Explain Kronig – Penny Model.	10	CO1	L3
<b>UNIT-II</b>				
4) a.	Classify extrinsic semiconductors. Compare n-type and p-type semiconductors.	6	CO2	L4
b.	Draw the V – I characteristics of a PN junction diode.	4	CO2	L3

Q.No	Question	M	CO	BL
<b>OR</b>				
5) a.	Write the statement of the Hall effect.	2	CO2	L3
b.	Derive expression for Hall voltage?	8	CO2	L4
<b>UNIT-III</b>				
6) a.	Define internal field?	2	CO3	L2
b.	Derive an expression for the internal field.	8	CO3	L3
<b>OR</b>				
7) a.	What is hysteresis?	2	CO3	L2
b.	Explain the hysteresis behavior of ferromagnetic materials with a neat diagram.	8	CO3	L3
<b>UNIT-IV</b>				
8) a.	Explain any one method in the top-down approach.	5	CO4	L3
b.	What are the applications of nanomaterials?	5	CO4	L2
<b>OR</b>				
9) a.	What are the properties of nanomaterials?	5	CO4	L2
b.	Compare various characterization techniques.	5	CO4	L3
<b>UNIT-V</b>				
10) a.	Explain the construction and working of CO <sub>2</sub> laser.	7	CO5	L3
b.	What are the applications of laser in the medical field.	3	CO5	L2
<b>OR</b>				
11) a.	Define acceptance angle and numerical aperture.	2	CO5	L2
b.	Derive expressions for them.	8	CO5	L3

Code: 23PH202

Hall Ticket No.:

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**NARSIMHAREDDY ENGINEERING COLLEGE**  
(UGC AUTONOMOUS)

I B.Tech II Semester (NR23) Regular Examination, July 2024

**APPLIED PHYSICS**

(Common to CE, EEE, ME, ECE, CSE (CS), CSE (AI&ML))

Maximum marks: 60

Time : 3 hours

- Note:
- This question paper contains two parts, A and B
  - Part A is compulsory which carries 10 marks (10 sub questions are two from each unit carry 1 Mark). Answer all questions in Part A
  - Part B Consists of 5 Units. Answer one question from each unit. Each question carries 10 Marks and may have a, b sub questions

**Part-A**

Answer all questions

(10 Marks)

Q.No	Question	M	CO	BL
1) a.	State Heisenberg's uncertainty principle.	1	CO1	L1
b.	Evaluate the wavelength of an electron accelerated with potential 100V.	1	CO1	L4
c.	List any two use of Zener diode.	1	CO2	L2
d.	Draw the symbol of n-p-n BJT.	1	CO2	L4
e.	Write the relation between D, E and P.	1	CO3	L3
f.	Define magnetostriiction.	1	CO3	L1
g.	What you understand about quantum confinement.	1	CO4	L2
h.	Why the one Nano meter is magical point on the dimension scale.	1	CO4	L5
i.	What is the main function of Optical Resonator?	1	CO5	L2
j.	Define acceptance angle.	1	CO5	L1

**Part-B**

Answer all the Units

(50 Marks)

All Questions carry equal Marks

Q.No	Question	M	CO	BL
<b>UNIT-I</b>				
2) a.	What is a black body? Demonstrate briefly the distribution of energy in a blackbody spectrum.	5	CO1	L3
b.	Identify the salient feature of Kronig-Penny Model.	5	CO1	L3
<b>OR</b>				
3) a.	Show that the energy of particle in a 1D box is quantised.	5	CO1	L3
b.	Choose any five differences between conductors, insulators and semiconductors based on the band theory of solids.	5	CO1	L3
<b>UNIT-II</b>				
4) a.	Compare direct and indirect band gap semiconductors.	5	CO2	L4
b.	Explain the principle and construction of LED.	5	CO2	L4
<b>OR</b>				
5) a.	What is Hall effect? Describe an experimental setup to measure the Hall voltage.	5	CO2	L4

b.	State the principle of solar cell? Discuss the construction of solar cell with neat sketch.	5	CO2	L4
<b>UNIT-III</b>				
6) a.	Distinguish between electronic, ionic, orientation polarizations.	5	CO3	L4
b.	What is hysteresis loop in Ferro magnet materials? What does it represent? What is its significance?	5	CO3	L3
<b>OR</b>				
7) a.	What is Ferro electricity? Mention the important properties of Ferro electric.	5	CO3	L3
b.	What are soft and hard magnetic materials? Give their characteristic properties.	5	CO3	L4
<b>UNIT-IV</b>				
8) a.	Discuss about various bottom up approach method for fabrication of Nano materials.	5	CO4	L4
b.	Explain the working of TEM.	5	CO4	L2
<b>OR</b>				
9) a.	Justify why the surface area to volume ratio is very large for nanoparticles compared to bulk materials?	5	CO4	L5
b.	Discuss various applications of Nano materials.	5	CO4	L3
<b>UNIT-V</b>				
10) a.	Write a note on construction of He-Ne gas Laser.	5	CO5	L2
b.	List the applications of fiber optics in various fields.	5	CO5	L3
<b>OR</b>				
11) a.	Explain the working of semiconductor laser diode.	5	CO5	L2
b.	Discuss about fiber optic communication with suitable diagram.	5	CO5	L3

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**NARSIMHAREDDY ENGINEERING COLLEGE**  
(UGC AUTONOMOUS)

I.B.Tech I Semester (NR23) Supplementary Examination, July 2024

**APPLIED PHYSICS**

(Common to CSE, IT)

Time : 3 hours

Maximum marks: 60

- This question paper contains two parts, A and B
- Part A is compulsory which carries 10 marks (10 sub questions are two from each unit carry 1 Marks). Answer all questions in Part A
- Part B Consists of 5 Units. Answer one question from each unit. Each question carries 10 Marks and may have a, b sub questions

**Part-A**  
Answer all questions

(10 Marks)

Q.No	Question	M	CO	BL
1) a	Write an expression for Stefan-Boltzmann law?	1	CO1	L1
b	Find the minimum energy level for an electron in a 1-D potential box	1	CO1	L1
c	Draw Fermi (EF) energy level in intrinsic, p- type and n-types semiconductors.	1	CO2	L2
d	Distinguish between direct and indirect bandgap semiconductors?	1	CO1	L2
e	Define dielectric polarization. Classify?	1	CO1	L1
f	Mention few applications of magnetic field sensors?	1	CO1	L2
g	Classify the nanomaterials.	1	CO1	L1
h	What are the advantages of nanomaterials?	1	CO1	L1
i	Define pumping?	1	CO1	L1
j	Calculate the acceptance angle of an optical fiber of core and cladding of refractive indices 1.45 and 1.30.	1	CO1	L3

**Part-B**

(50 Marks)

Answer all the Units  
All Questions carry equal Marks

Q.No	Question	M	CO	BL
<b>UNIT-I</b>				
2) a	Distinguish between electromagnetic wave and matter wave?	3	CO1	L3
b	Explain de Broglie's hypothesis.	7	CO1	L3
<b>OR</b>				
3) a	Discuss Drude - Lorentz's theory of free electrons.	6	CO1	L4
b	Classify solids based on energy bands.	4	CO1	L2
<b>UNIT-II</b>				
4) a	Compare direct and indirect band gap semiconductors.	6	CO2	L3
b	Explain the construction and working of LED.	4	CO2	L2
<b>OR</b>				

5) a	What is a bipolar junction transistor? Identify its parts?	3	CO2	L2
b	Explain various methods of transistor configuration. Which configuration of most suitable?	7	CO2	L3
<b>UNIT-III</b>				
6) a	Define electric dipole, dipole moment, and susceptibility.	3	CO3	L2
b	Deduce expression for Clausius - Mosotti equation.	7	CO3	L3
<b>OR</b>				
7) a	Explain the domain theory of ferromagnetism.	5	CO3	L2
b	Distinguish between soft and hard magnetic materials.	5	CO3	L4
<b>UNIT-IV</b>				
8) a	Explain quantum confinement and surface-to-volume ratio.	6	CO4	L3
b	What are the various applications of nanomaterials.	4	CO4	L2
<b>OR</b>				
9) a	Explain the ball milling method.	5	CO4	L3
b	What is the principle of the XRD method? Mention a few applications of nanomaterials.	5	CO4	L2
<b>UNIT-V</b>				
10) a	Explain Einstein's coefficients.	7	CO5	L2
b	List the various methods in pumping.	3	CO5	L3
<b>OR</b>				
11) a	Label various parts of an optical fiber using a neat diagram.	3	CO5	L3
b	Explain optical fiber communication system.	7	CO5	L3

Code No: 132AF

R16

JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY, HYDERABAD

B.Tech I Year II Semester Examinations, May - 2019

APPLIED PHYSICS

(Common to CE, ME, MCT, AE, MIE, PTM, CEE, MSNT)

Time: 3 hours

Max. Marks: 75

**Note:** This question paper contains two parts A and B.  
Part A is compulsory which carries 25 marks. Answer all questions in Part A.  
Part B consists of 5 Units. Answer any one full question from each unit. Each question carries 10 marks and may have a, b, c as sub questions.

**PART- A**

- (25 Marks)
- 1.a) Define stress, strain and write their units. [2]
  - b) Define Poisson's ratio. [3]
  - c) What is the Sabine's formula? Explain [2]
  - d) What is acoustic quieting? [3]
  - e) What is Piezoelectric effect? [2]
  - f) What are the properties of ultrasonics? [3]
  - g) Explain dielectric constant & electrical susceptibility. [2]
  - h) Distinguish between Ferro-electricity and Piezoelectricity. [3]
  - i) What is Bohr magneton? [2]
  - j) Explain ferromagnetism. [3]

**PART-B**

(50 Marks)

2. What is the Torsional pendulum? Explain how it is used to determine the rigidity modulus of a given wire. [10]
- OR**
3. Derive the relation between three modules of elasticity. [10]
  4. Explain various factors affecting architectural acoustics and their remedies. [10]
- OR**
- 5.a) What are the requisites for good acoustics?  
b) Describe the method of measurement of sound absorption coefficient. [4+6]
  6. Explain how the ultrasonic waves produced with the help of piezoelectric method. [10]
- OR**
7. Describe in detail applications of ultrasonic waves [10]

8.a) Explain the electronic polarizability in atoms and obtain an expression for electronic polarizability in terms of the radius of the atom.

b) The radius of a gaseous atom is 0.062nm. Calculate the electronic polarizability of the gas and its relative permittivity. Given that the number of atoms of the gas is  $2.7 \times 10^{25}$  per  $m^3$ . [8+2]

OR

9.a) Explain in detail the structure of  $BaTiO_3$  and write its applications.

b) Derive an expression for ionic polarizability in an ionic solid. [5+5]

10.a) Explain the origin of magnetic moment and also explain classification of magnetic materials.

b) Describe Hysteresis behavior of ferromagnetic material. [5+5]

OR

11.a) Describe the properties of superconductors.

b) What are important applications of superconductors? Explain in detail. [4+6]

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16-05-2019AM

R18

Code No: 151AE

JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD

B.Tech I Year I Semester Examinations, September/October - 2021

APPLIED PHYSICS

(Common to ECE, EIE, ECM, CSBS, CSE(AI&ML), CSE(IOT))

Time: 3 Hours

Max. Marks: 75

Answer any five questions  
All questions carry equal marks

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- 1.a) Show that the energies of a particle in a one dimensional potential box are quantized.  
b) Find the probability of finding a particle between  $0.35a$  and  $0.65a$  where 'a' is the width of the box and particle is in the first excited state. [10+5]
- 2.a) Describe the Davisson and Germer's experimental for verification of matter waves.  
b) Electrons are accelerated through 344 volts and are reflected from a crystal. The first reflection maximum occurs when glancing angle is  $60^\circ$ . Determine the spacing of the crystal. Given  $h = 6.62 \times 10^{-34}$  Joule-sec,  $e = 1.6 \times 10^{-19}$  C and  $m_e = 9 \times 10^{-31}$  kg. [10+5]
- 3.a) What is a PN-junction diode? Discuss the V-I characteristics of a diode in both the biasing conditions.  
b) Explain advantage of Zener diode over P-N junction diode. [10+5]
- 4.a) Explain the Hall effect in metal? Derive the formulae to determine Hall coefficient and mobility of electrons.  
b) An n-type germanium sample has a donor density of  $10^{21}/m^3$ . It is arranged in a Hall experiment having magnetic field of 0.5T and the current density is  $500 A/m^2$ . Find the Hall voltage if the sample is 3mm wide. [10+5]
- 5.a) What is an LED? Explain the working of LED with a neat diagram.  
b) Write a short note on solar cell. [10+5]
- 6.a) What are semiconductor diode lasers? Describe the construction and working of a semiconductor laser with energy band diagram.  
b) Discuss advantages of diode lasers over gas lasers. [10+5]
- 7.a) Draw the block diagram of an optical fibre communication system and explain the function of each block.  
b) Consider a fibre having a core of index 1.48, a cladding of index 1.46 and has a core diameter of 30 mm. Show that all rays making an angle less than  $9.43^\circ$  with the axis will propagate through the fibre. [10+5]
- 8.a) State and explain the basic laws of electromagnetism in their integral form.  
b) Distinguish between conduction current and displacement current. [10+5]

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Answer any five questions

All questions carry equal marks

1. (a) Explain the concept of a particle with an unbounded energy by discussing the case of a free particle. (100)
- (b) Find the probability of finding a free electron with a kinetic energy of 10 eV in the first two energy levels in a one-dimensional infinite potential well. (100)
2. (a) Describe the physical mechanism of the formation of a PN junction diode. (100)
- (b) Explain the operation of a PN junction diode under forward bias. (100)
3. (a) What is a P-N junction diode? Explain the V-I characteristics of a diode in both forward and reverse bias. (100)
- (b) Explain the Hall effect in metals. Draw the diagram to determine Hall coefficient and polarity of electrons. (100)
4. (a) For a type III semiconductor, the band gap is 0.5 eV. It is doped with a donor impurity having magnetic field of 0.5 T and the spin splitting is 0.05 eV. Find the Hall voltage if the carrier density is  $10^{21} \text{ m}^{-3}$ . (100)
- (b) Write a short note on quantum wells. (100)
5. (a) What are semiconductor device bases? Discuss the construction and working of a MOSFET. (100)
- (b) Discuss advantages of thin layer over bulk. (100)
6. (a) Draw the block diagram of an optical fiber communication system and explain the function of each block. (100)
- (b) Consider a fiber having a core of index 1.5, a cladding of index 1.45 and core diameter of 30  $\mu\text{m}$ . Show that all rays making an angle less than  $9.5^\circ$  with the axis will propagate through the fiber. (100)
7. (a) Present and explain the basic laws of photoconduction in their integral form. (100)
- (b) Distinguish between conduction current and displacement current. (100)

R18

Code No: 152AE

JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD

B.Tech I Year II Semester Examinations, November/December - 2020

APPLIED PHYSICS

(Common to CSE, IT, ITE)

Time: 2 hours

Max. Marks: 75

Answer any five questions

All questions carry equal marks

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- 1.a) What is Compton effect? Explain in detail.
- b) Calculate the velocity and kinetic energy of an electron having wavelength of 0.21nm. [9+6]
- 2.a) Discuss Born's interpretation of the wave function.
- b) Derive the expression for de-Broglie's wavelength. [7+8]
- 3.a) Discuss n-type semiconductors fermi level variation with respect to carrier concentration and temperature.
- b) Derive an expression for carrier generation and recombination. [8+7]
- 4.a) What is Hall effect? Derive an expression of Hall Coefficient.
- b) Distinguish between n- type and p-type semiconductors. [9+6]
- 5.a) Write a note on Avalanche photodiode.
- b) What is a radiative and non- radiative recombination mechanism in semiconductors? [9+6]
- 6.a) Describe in detail with a neat diagram LED construction and working principle.
- b) What are the characteristics of Solar cell? [9+6]
- 7.a) With necessary theory and energy level diagram explain the working of He-Ne gas laser.
- b) Write a note on Losses associated with optical fibers. [9+6]
- 8.a) Obtain an expression for the Internal field seen by an atom in an infinite array of atoms subjected to an external field.
- b) Write a note on ferromagnetic domains. [9+6]

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R18

Code No: 152AE

JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD

B.Tech I Year II Semester Examinations, September/October - 2021

APPLIED PHYSICS

(Common to EEE, CSE, IT, CSIT, ITE, CE(SE), CSE(CS), CSE(DS), CSE(Networks))

Time: 3 Hours

Max. Marks: 75

Answer any five questions  
All questions carry equal marks

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- 1.a) In detail describe Photoelectric effect.
- b) Discuss Heisenberg's Uncertainty principle. [7+8]
- 2.a) Write a note on Carrier generation and recombination.
- b) Explain Photo-electric effect and Compton Effect in detail. [7+8]
- 3.a) Describe formation of depletion region in p-n junction diode.
- b) Explain operation of principle of BJT.
- c) What are the applications of p-n junction diode? [6+6+3]
4. Explain about Zener diode with its characteristics. [15]
5. What is Lasing action? Explain in detail. Discuss construction and working of semiconductor lasers with diagram. [15]
6. With suitable diagram explain construction and working principle of He-Ne laser system. [15]
- 7.a) What are losses associated with optical fibers? Explain in detail.
- b) What is "total internal reflection"? Discuss about applications of Optical fibers. [7+8]
8. Discuss in detail about "Hysteresis loop". Mention some of the applications of magnetic materials. [15]

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